

April 1995

30A, 700V - 1000V Hyperfast Diodes

**Features**

- Hyperfast with Soft Recovery ..... <65ns
- Operating Temperature ..... +175°C
- Reverse Voltage Up To ..... 1000V
- Avalanche Energy Rated
- Planar Construction

**Applications**

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

**Description**

RHRG3070, RHRG3080, RHRG3090 and RHRG30100 (TA49064) are hyperfast diodes with soft recovery characteristics ( $t_{RR} < 65ns$ ). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

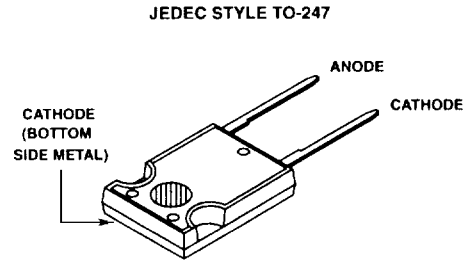
These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

**PACKAGING AVAILABILITY**

| PART NUMBER | PACKAGE | BRAND     |
|-------------|---------|-----------|
| RHRG3070    | TO-247  | RHRG3070  |
| RHRG3080    | TO-247  | RHRG3080  |
| RHRG3090    | TO-247  | RHRG3090  |
| RHRG30100   | TO-247  | RHRG30100 |

NOTE: When ordering, use the entire part number.

**Package**



**Symbol**



**Absolute Maximum Ratings**  $T_C = +25^\circ C$ , Unless Otherwise Specified

|  | RHRG3070    | RHRG3080    | RHRG3090    | RHRG30100   | UNITS      |
|--|-------------|-------------|-------------|-------------|------------|
| Peak Repetitive Reverse Voltage ..... $V_{RRM}$                                | 700         | 800         | 900         | 1000        | V          |
| Working Peak Reverse Voltage ..... $V_{RWM}$                                   | 700         | 800         | 900         | 1000        | V          |
| DC Blocking Voltage ..... $V_R$  | 700         | 800         | 900         | 1000        | V          |
| Average Rectified Forward Current ..... $I_{F(AV)}$<br>( $T_C = +95^\circ C$ ) | 30          | 30          | 30          | 30          | A          |
| Repetitive Peak Surge Current ..... $I_{FSM}$<br>(Square Wave, 20kHz)          | 70          | 70          | 70          | 70          | A          |
| Nonrepetitive Peak Surge Current ..... $I_{FSM}$<br>(Halfwave, 1 Phase, 60Hz)  | 325         | 325         | 325         | 325         | A          |
| Maximum Power Dissipation..... $P_D$   | 125         | 125         | 125         | 125         | W          |
| Avalanche Energy (See Figures 10 and 11)..... $E_{AVL}$                        | 20          | 20          | 20          | 20          | mj         |
| Operating and Storage Temperature ..... $T_{STG}, T_J$                         | -65 to +175 | -65 to +175 | -65 to +175 | -65 to +175 | $^\circ C$ |

7  
HYPERFAST  
SINGLE DIODES

## Specifications RHRG3070, RHRG3080, RHRG3090, RHRG30100

### Electrical Specifications $T_C = +25^\circ\text{C}$ , Unless Otherwise Specified

| SYMBOL          | TEST CONDITION  | RHRG3070 |     |     | RHRG3080 |     |     | RHRG3090 |     |     | RHRG30100 |     |     | UNITS                     |
|-----------------|---|----------|-----|-----|----------|-----|-----|----------|-----|-----|-----------|-----|-----|---------------------------|
|                 |   | MIN      | TYP | MAX | MIN      | TYP | MAX | MIN      | TYP | MAX | MIN       | TYP | MAX |                           |
| $V_F$           | $I_F = 30\text{A}, T_C = +25^\circ\text{C}$           | -        | -   | 3.0 | -        | -   | 3.0 | -        | -   | 3.0 | -         | -   | 3.0 | V                         |
|                 | $I_F = 30\text{A}, T_C = +150^\circ\text{C}$          | -        | -   | 2.5 | -        | -   | 2.5 | -        | -   | 2.5 | -         | -   | 2.5 | V                         |
| $I_R$           | $V_R = 700\text{V}, T_C = +25^\circ\text{C}$          | -        | -   | 250 | -        | -   | -   | -        | -   | -   | -         | -   | -   | $\mu\text{A}$             |
|                 | $V_R = 800\text{V}, T_C = +25^\circ\text{C}$          | -        | -   | -   | -        | -   | 500 | -        | -   | -   | -         | -   | -   | $\mu\text{A}$             |
|                 | $V_R = 900\text{V}, T_C = +25^\circ\text{C}$          | -        | -   | -   | -        | -   | -   | -        | -   | 500 | -         | -   | -   | $\mu\text{A}$             |
|                 | $V_R = 1000\text{V}, T_C = +25^\circ\text{C}$         | -        | -   | -   | -        | -   | -   | -        | -   | -   | -         | -   | 500 | $\mu\text{A}$             |
| $I_R$           | $V_R = 700\text{V}, T_C = +150^\circ\text{C}$         | -        | -   | 1.0 | -        | -   | -   | -        | -   | -   | -         | -   | -   | mA                        |
|                 | $V_R = 800\text{V}, T_C = +150^\circ\text{C}$         | -        | -   | -   | -        | -   | 1.0 | -        | -   | -   | -         | -   | -   | mA                        |
|                 | $V_R = 900\text{V}, T_C = +150^\circ\text{C}$         | -        | -   | -   | -        | -   | -   | -        | -   | 1.0 | -         | -   | -   | mA                        |
|                 | $V_R = 1000\text{V}, T_C = +150^\circ\text{C}$        | -        | -   | -   | -        | -   | -   | -        | -   | -   | -         | -   | 1.0 | mA                        |
| $t_{RR}$        | $I_F = 1\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$  | -        | -   | 65  | -        | -   | 65  | -        | -   | 65  | -         | -   | 65  | ns                        |
|                 | $I_F = 30\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | -        | -   | 75  | -        | -   | 75  | -        | -   | 75  | -         | -   | 75  | ns                        |
| $t_A$           | $I_F = 30\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | -        | 35  | -   | -        | 35  | -   | -        | 35  | -   | -         | 35  | -   | ns                        |
| $t_B$           | $I_F = 30\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | -        | 33  | -   | -        | 33  | -   | -        | 33  | -   | -         | 33  | -   | ns                        |
| $Q_{RR}$        | $I_F = 30\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$ | -        | 200 | -   | -        | 200 | -   | -        | 200 | -   | -         | 200 | -   | nC                        |
| $C_J$           | $V_R = 10\text{V}, I_F = 0\text{A}$                   | -        | 100 | -   | -        | 100 | -   | -        | 100 | -   | -         | 100 | -   | pF                        |
| $R_{\theta JC}$ |   | -        | -   | 1.2 | -        | -   | 1.2 | -        | -   | 1.2 | -         | -   | 1.2 | $^\circ\text{C}/\text{W}$ |

#### DEFINITIONS

$V_F$  = Instantaneous forward voltage ( $p_w = 300\mu\text{s}$ ,  $D = 2\%$ ).

$I_R$  = Instantaneous reverse current.

$t_{RR}$  = Reverse recovery time (Figure 2), summation of  $t_A + t_B$ .

$t_A$  = Time to reach peak reverse current (See Figure 2).

$t_B$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 2).

$Q_{RR}$  = Reverse recovery charge.

$C_J$  = Junction Capacitance.

$R_{\theta JC}$  = Thermal resistance junction to case.

$E_{AVL}$  = Controlled avalanche energy. (See Figures 10 and 11).

$p_w$  = pulse width.

$D$  = duty cycle.

$V_1$  AMPLITUDE CONTROLS  $I_F$   
 $V_2$  AMPLITUDE CONTROLS  $di_F/dt$   
 $L_1$  = SELF INDUCTANCE OF  
 $R_4 + L_{\text{LOOP}}$

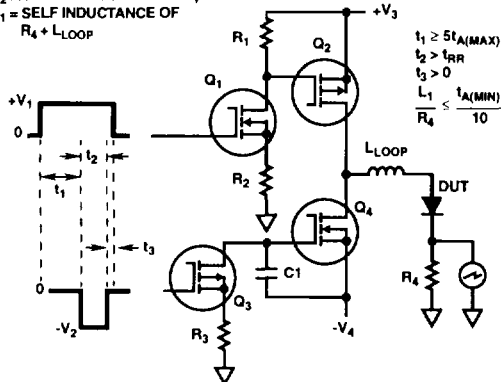


FIGURE 1.  $t_{RR}$  TEST CIRCUIT

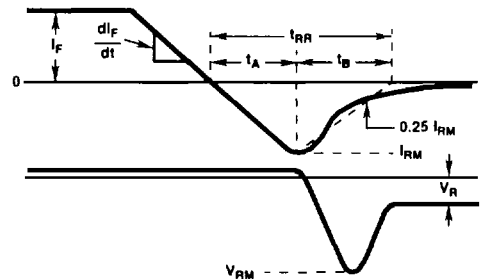


FIGURE 2.  $t_{RR}$  WAVEFORMS AND DEFINITIONS

Typical Performance Curves

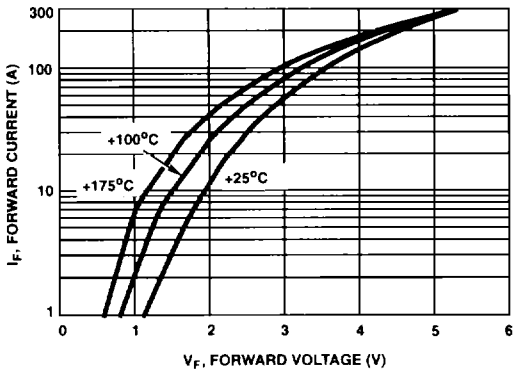


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

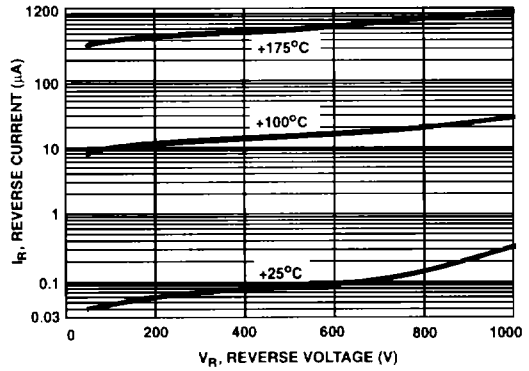


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

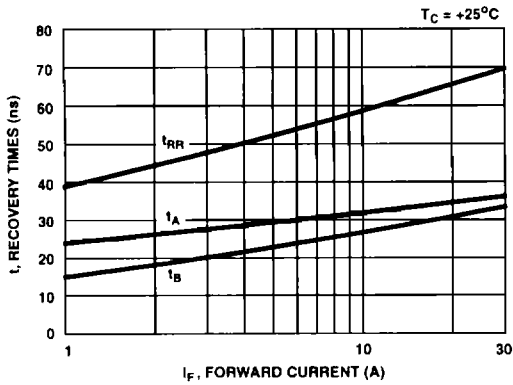


FIGURE 5. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT AT +25°C

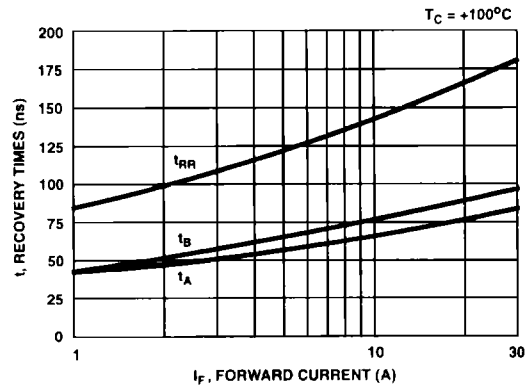


FIGURE 6. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT AT +100°C

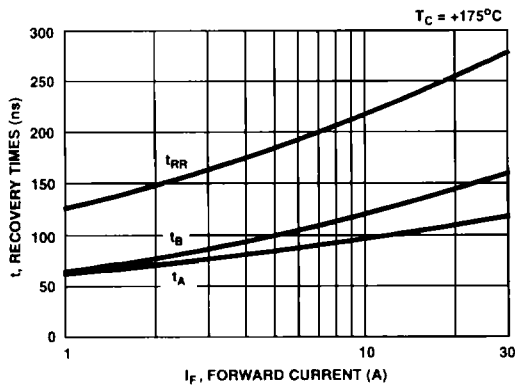


FIGURE 7. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT AT +175°C

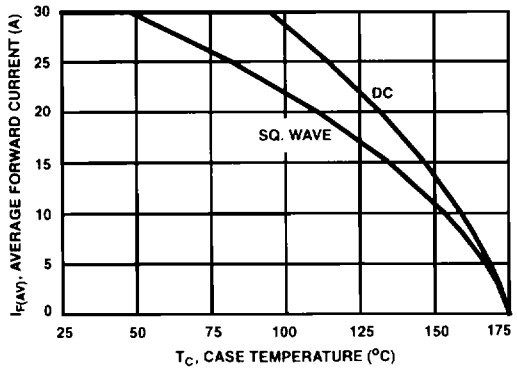


FIGURE 8. CURRENT DERATING CURVE FOR ALL TYPES

Typical Performance Curves (Continued)

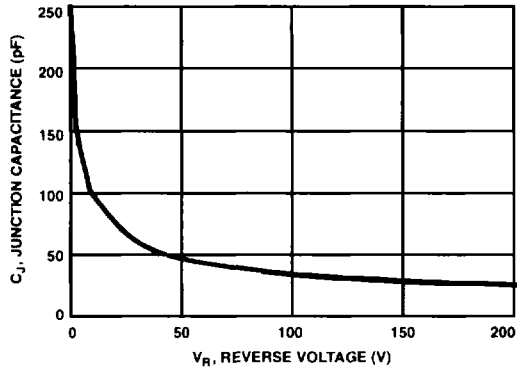


FIGURE 9. TYPICAL JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuit and Waveforms

$I_{MAX} = 1A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2 L I_L^2 [V_{AVL} / (V_{AVL} - V_{DD})]$   
 $Q_1$  AND  $Q_2$  ARE 1000V MOSFETs

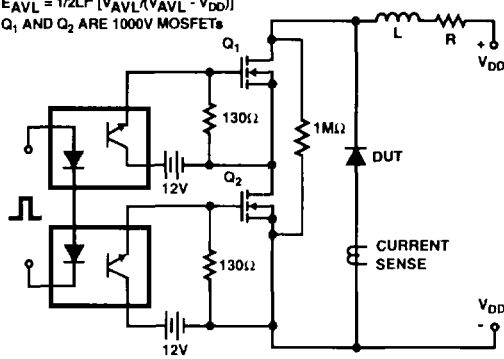


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

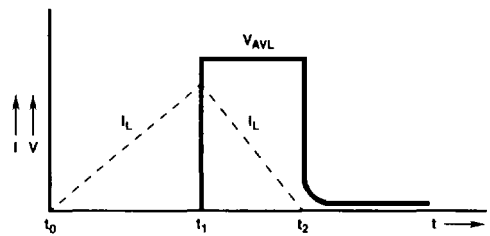


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS